

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- High blocking voltage capability
- Direct triggering from low power drivers and logic ICs
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Low holding current for low current loads and lowest EMI at commutation
- Sensitive gate

3. Applications

- General purpose motor control
- General purpose switching

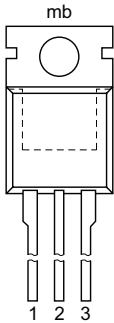
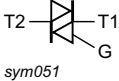
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute maximum rating							
V _{DRM}	repetitive peak off-state voltage		600				V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 102 °C; Fig. 1 ; Fig. 2 ; Fig. 3	8				A
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; Fig. 4 ; Fig. 5	65				A
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7		-	2.5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7		-	4	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7		-	5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; Fig. 7		-	11	25	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 9		-	2.5	20	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT137-600E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT137-600E	BT137-600E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 102\text{ }^{\circ}\text{C}$; Fig 1 ; Fig 2 ; Fig 3	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; Fig 4 ; Fig 5	65	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 16.7\text{ ms}$	71	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; SIN	21	A^2s
dI_{T}/dt	rate of rise of on-state current	$I_{\text{G}} = 20\text{ mA}$; T2+ G+	50	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 20\text{ mA}$; T2+ G-	50	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 20\text{ mA}$; T2- G-	50	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 50\text{ mA}$; T2- G+	10	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		2	A
P_{GM}	peak gate power		5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	0.5	W
T_{stg}	storage temperature		-40 to 150	$^{\circ}\text{C}$
T_{j}	junction temperature		125	$^{\circ}\text{C}$

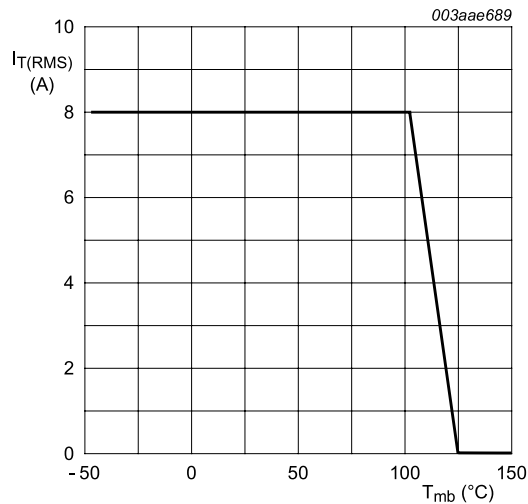


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

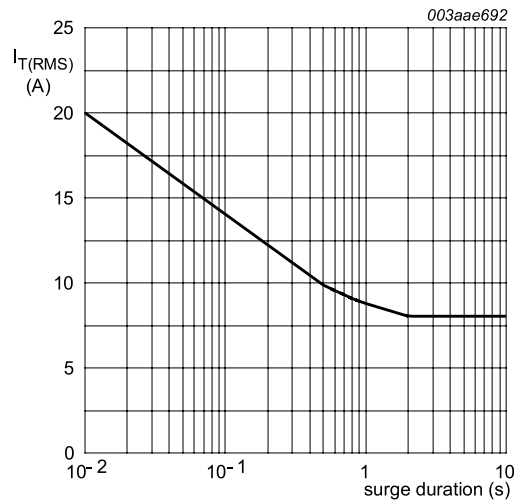


Fig. 2. RMS on-state current as a function of surge duration; maximum values
 $f = 50 \text{ Hz}; T_{mb} \leq 102 \text{ °C}$

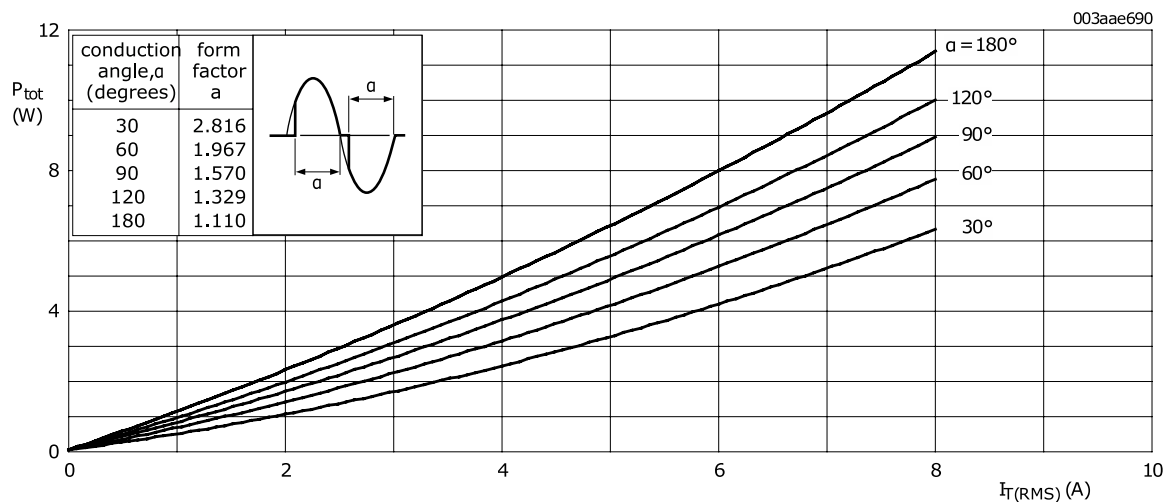
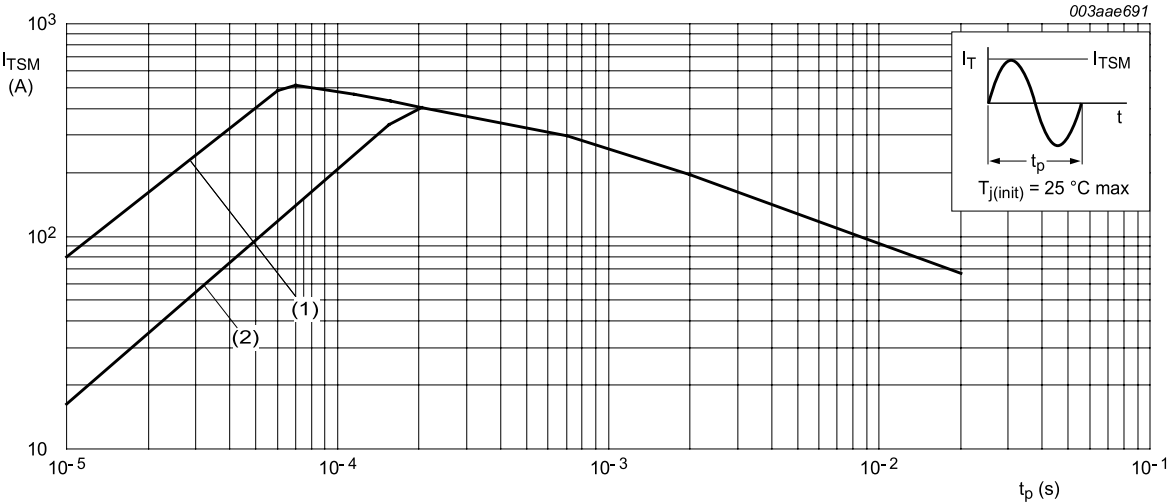
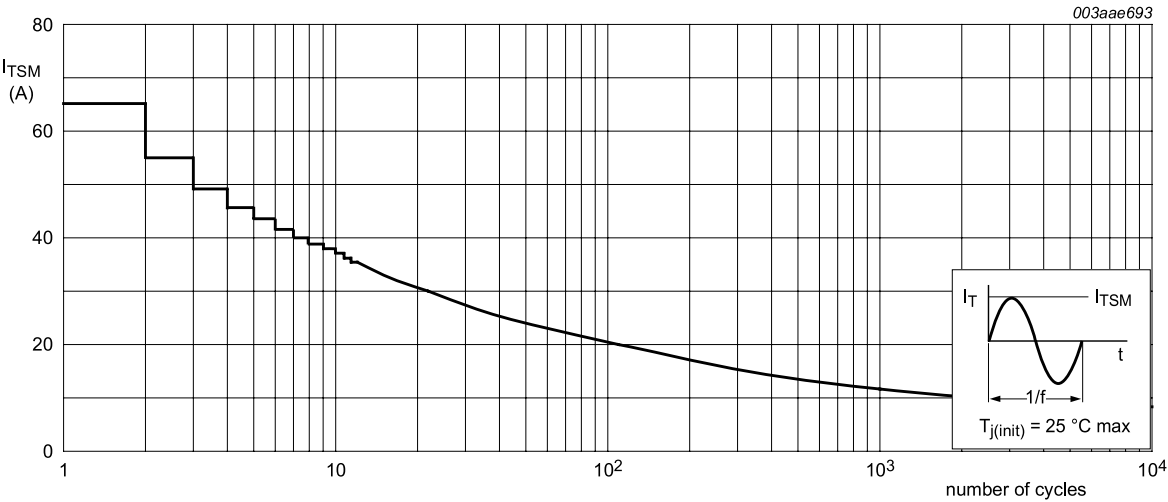


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



$t_p \leq 20\text{ ms}$
(1) dI_T/dt limit
(2) T2- G+ quadrant limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values



$f = 50\text{ Hz}$

Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig 6		-	-	2	K/W
		half cycle; Fig 6		-	-	2.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W

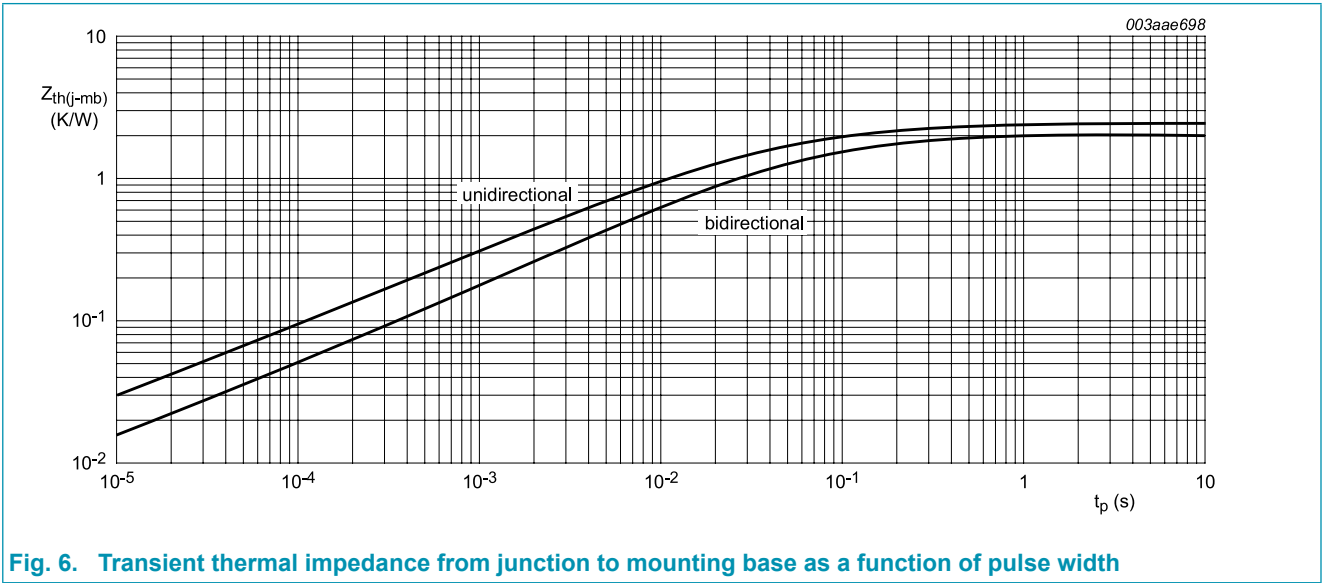
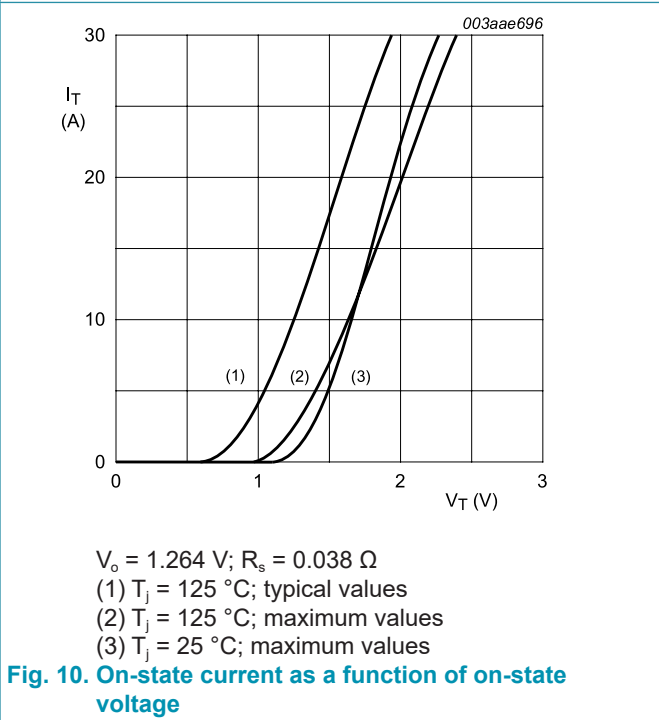
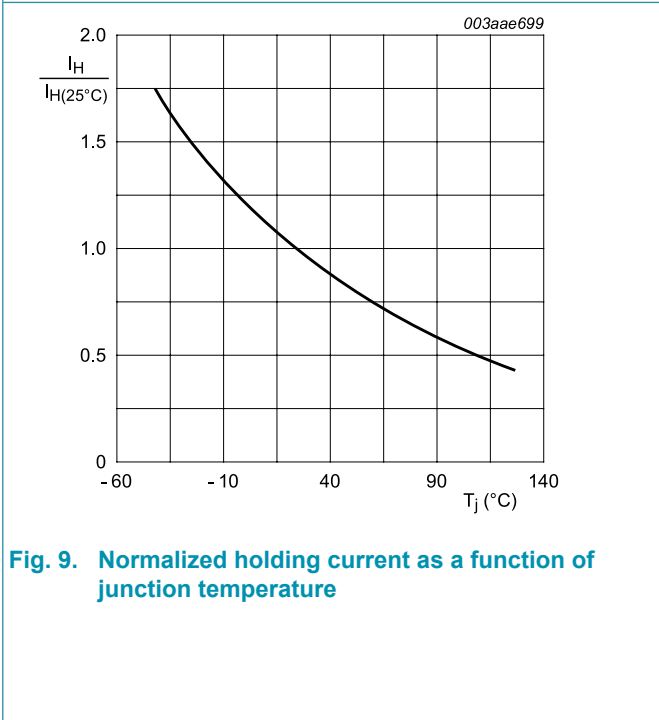
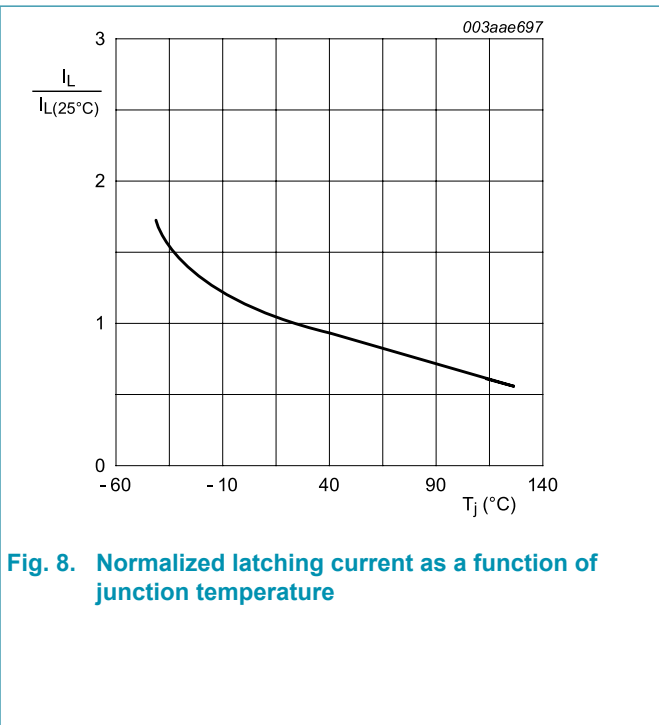
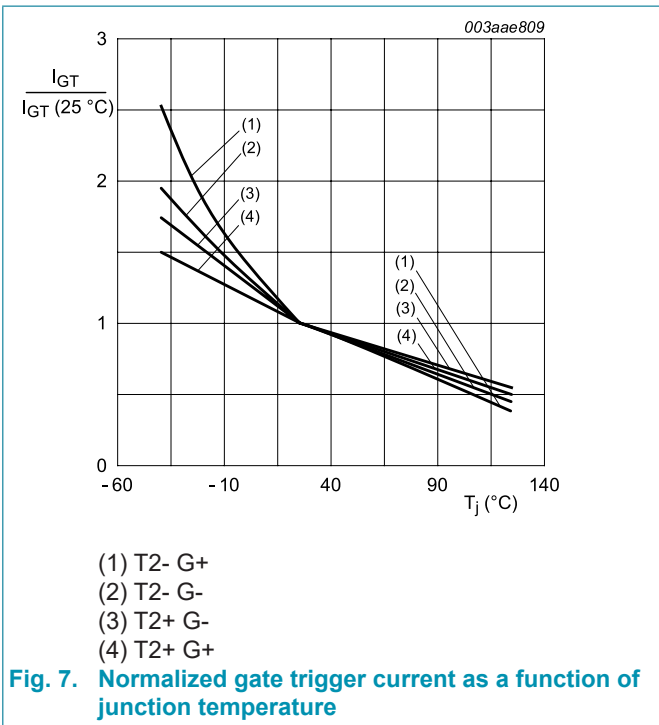


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	2.5	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	4	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	5	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	11	25	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	3	25	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	14	35	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	3	25	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	4	35	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		-	2.5	20	mA
V_T	on-state voltage	$I_T = 10\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 11		-	0.7	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 125\text{ }^\circ\text{C}$; Fig. 11		0.25	0.4	-	V
I_D	off-state current	$V_D = 600\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$		-	0.1	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		-	50	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 12\text{ A}$; $V_D = 600\text{ V}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$		-	2	-	μs



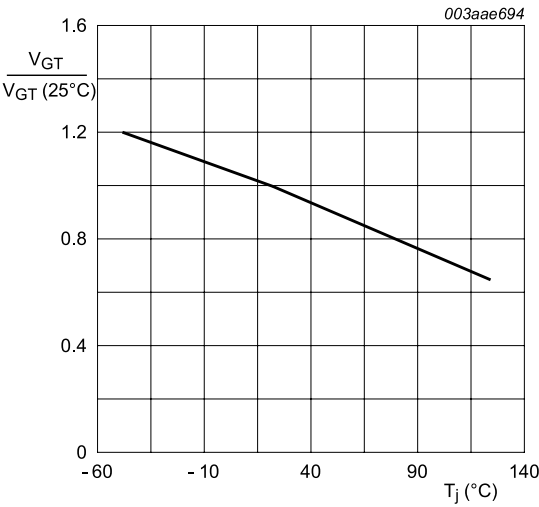


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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